IN THE CLAIMS:

1-8. Cancelled

9. (Withdrawn)A method for stripping a liquid crystal display (LCD) surface, the method comprising:

forming a first electrically conducting layer;

forming an ozone resistive barrier overlying the first electrically conducting layer;

forming a metal layer overlying the ozone resistive barrier; forming a photoresist pattern with openings exposing overlying areas of the metal layer;

through the openings in the photoresist, etching the exposed metal layer and underlying ozone resistant barrier; and,

stripping the photoresist with an ozone compound.

- 10. (Withdrawn) The method of claim 9 wherein forming a first electrically conducting layer includes forming a conducting layer from indium tin oxide (ITO).
- 11. (Withdrawn) The method of claim 9 wherein forming an ozone resistant barrier overlying the first electrically conducting layer includes forming an ozone resistant barrier from a material selected from the group including Ta, Ti, TaN, TiN, Al, Al compounds, tungsten, chrome, and copper.

- 12. (Withdrawn) The method of claim 9 wherein forming a metal layer overlying the ozone resistant barrier includes forming a reflective metal layer from Al.
- 13. (Withdrawn) The method of claim 12 wherein forming a metal layer overlying the ozone resistant barrier includes forming a layer of Al having a thickness of greater than 1000 Å.
- 14. (Withdrawn) The method of claim 13 in which a reflective LCD structure is being stripped;

wherein forming a first electrically conducting layer includes forming an ITO electrode;

wherein forming an ozone resistant barrier overlying the first electrically conducting layer includes forming an ozone resistant barrier from a material selected from the group including Ta, Ti, TaN, and TiN;

wherein forming a metal layer overlying the ozone resistant barrier includes forming an Al layer; and.

the method further comprising:

following the ozone stripping, leaving an LCD reflector structure.

15. (Withdrawn) The method of claim 14 wherein stripping the photoresist with an ozone compound includes stripping with a compound having 85 parts per million (PPM) of ozone, or greater.

- 16. (Withdrawn) The method of claim 14 wherein stripping the photoresist with an ozone compound includes exposing the IC to the ozone compound for approximately 45 minutes.
- 17. (Withdrawn) The method of claim 14 wherein forming a metal layer overlying the ozone resistant barrier includes forming an Al layer having a thickness of greater than 1000 Å; and,

wherein stripping the photoresist with an ozone compound includes removing approximately 800~Å of Al exposed by the openings in the photoresist.

18. (Currently Amended) A liquid crystal display (LCD) reflector structure resistant to ozone stripping, the reflector structure comprising:

a first electrically conducting layer of indium tin oxide (ITO); an ozone resistive barrier overlying the first electrically conducting layer from a material selected from the group including Ti, Ta, TaN, Al, Al compounds, tungsten, and copper; and,

a metal layer overlying the ozone resistive barrier.

19-20. (Cancelled)

21. (Original) The reflector structure of claim 18 wherein the metal layer is a reflective metal layer material selected from the group including Al.

22. (Currently Amended) A liquid crystal display (LCD) reflector structure resistant to ozone stripping, the reflector structure comprising:

a first electrically conducting layer <u>electrode</u> of indium tin oxide (ITO);

an ozone resistive barrier overlying the first electrically conducting layer selected from the group including Ti, Ta, TaN, Al, Al compounds, tungsten, and copper; and,

an Al <u>LCD reflector</u> reflective metal layer overlying the ozone resistive barrier.

23-29. Cancelled

- 30. (New) The method of claim 18 wherein forming a metal layer overlying the ozone resistant barrier includes forming a layer of Al having a thickness of greater than 1000 Å.
- 31. (New) The method of claim 22 wherein forming an Al LCD reflector metal layer overlying the ozone resistive barrier includes forming a layer of Al having a thickness of greater than 1000 Å.